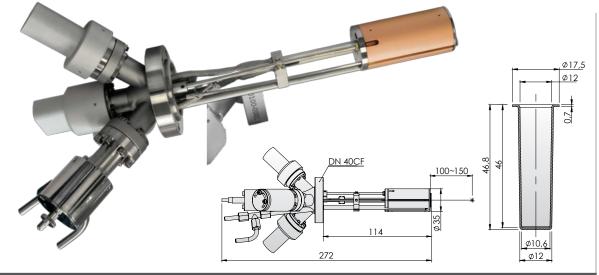
EF 40C1 EFFUSION CELL





DESCRIPTION

EF 40C1 Effusion Cell (Knudsen Cell) is a source designed for delivering highly constant evaporation rates by indirect resistive heating at the material. Custom insertion length 114 - 380 mm (other on request).

FEATURES

- Extremely stable flux rates
- Various crucible materials
- Highly reproducible & reliable
- Suitable for use in any MBE system
- Mo free construction (allows high outgassing temperatures)
- Integral water cooling

OPTIONS

- Customised insertion length
- With or without integrated manual/electro-pneumatic shutter
- Linear shift
- Crucibles
- Thermocouple type K

HEATING CONTROL APPLICATION

- wiin or wiinoui iniegralea manual/electro-pneumatic shutter
- Linear shift
- Crucibles

Mounting flange DN 40 CF (rotatable) Heater W wire (tungsten) Temperature range EF 1500 °C (~250 °C - 1500 °C, 1600 °C for degas) EF 1200 °C (~250 °C - 1200 °C) Temperature stability ± 0.1 °C

TECHNICAL DATA

Type of shutter

Water cooling

Working pressure

Temperature stability	± 0.1 °C
Crucible type (option)	PBN, Al ₂ O ₃ , Quartz (other materials on request)
Crucibles volume	5cc
Evaporated materials	all typical materials according to crucible type
Thermocouple type	EF 1500 °C - type C (standard) EF 1200 °C - type K (option)
Degassing temp.	1600 °C

(required)	temperature: 20 - 30 °C max pressure: 6 bar
Insertion length	min. 114 mm (other on request) OD: 35 mm
Deposition area	dependent on working distance
Working distance	100 - 150 mm
Bakeout temperature	up to 250 °C

< 10⁻⁵ mbar

water flow > 0.5 I/min

side or flip type, manual or pneumatic

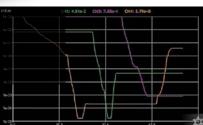


HEAT3-PS

SAMPLE HEATING POWER SUPPLY







Real time pressure charts (data export possibility).

DESCRIPTION

The HEAT3-PS is used for resistive heating or electron bombardment heating. The power supply can also be used for effusion cell evaporators. The unit is equipped with a PID temperature controller. Ramp heating function control sample temperature to protect sample from damage. Sample overheating can also be protected by setting the voltage and current limits. The unit can be operated in auto mode (with temperature control) or manual mode (without temperature control). The unit is equipped with autosave function (the device save your parameters, preset and apply them automatically after restart).

FEATURES

- Dual heating mode: resistive and electron bombardment
- Wide range temperature measurement (1.4 2473.15 K)
- 2D real time chart module
- High efficiency
- Setpoint based over-voltage and over-current output protection
- Fully manual or PID temperature controlled (by setpoint and ramp)
- Process temperature control with built-in PID controller (with autotuning function for optimized process PID parameters)
- Various kind of temperature sensors: thermocouples K/C/ E/N (other on request), Pt, diode
- Multiple I/O (10 digital/4 analog) individual reprogrammable
- High resolution (16-bit analog I/O, 0.1 K temp.)
- One vacuum channel for active gauges
- Shutter control function up to 2* shutters (e.g. shutters of sources or manipulators)
- Mobile solutions for remote access and control
- Customised menu options (for robust and effectivity)
- Support (easy firmware update via USB)
- * for double DC module version, 1 shutter per channel

OPTIONS

- Second DC module available: two resistive heating zones with independent control, or one resistive heating zone with higher output power (90V, 17A or 45V, 30A) excluding EB module
- Analog I/O card for vacuum measurement (1 gauge)

TECHNICAL DATA

Supply voltage	100-130VAC/200-260 VAC, 50-60Hz
	(power consumption max 1600 W)

Resistive heating 45 V, 17 A - standard; mode parameters other versions on request

EB heating 1000 V, 300 mA - standard; mode parameters other versions on request

Temperature	- 273.15 K - 2473.15 K for type C thermocouple
range	(dependent on sample holder type or evaporator)

(dependent on sample holder type or evaporator)

73.15 K - 1645.15 K for type K thermocouple

1.4 K - 500 K for DT670/DT470 silicon diodes

(dependent on sample holder type and conditions in chamber)

emperature	2 - for thermocouples K/C/E/N
ndenendent	2 for silican diades DT470/DT470

Temperature adjustable from 0.1 K to 1000 K/s|min|h setpoint ramp rate

ΔT setpoint 0.1 to 5.0 K/s

Communication R\$232/485, Ethernet interface

protocol	
User interface	7" TFT display with touchscreen.

MODBUS-TCP

digital encoder

Interface	English, German, Polish
languages	

Dimensions	448.8 × 132.5 × 375 mm (W×H×D),
	19" rack mountable

Weight (approx.) 8.8 kg (for standard version)

APPLICATION

Communication

inputs

- Any thermal process according to the specifications
- Effusion cells supply
- Sample holders heating
- Thermal monitoring

